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Responsible committee: EPL/47 Semiconductors

Interested committees:

Title: Draft BS EN 63378-3 Ed.1.0 Thermal standardization on semiconductor packages. Part 3: Thermal circuit simulation models of semiconductor packages for transient analysis.

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- ii) affects other national standard(s)
- iii) requires additional national guidance or information

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This draft standard is based on national and international discussions. Your comments on this draft are invited and will assist in the preparation of the consequent standard.

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UK Vote

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Template for comments and secretariat observations

Date: xx/xx/20xx	Document: ISO/DIS xxxx
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1	2	(3)	4	5	(6)	7
MB	Clause No./ Subclause No./Annex (e.g. 3.1)	Paragraph/ Figure/Table/Note	Type of comment	Comment (justification for change) by the MB	Proposed change by the MB	Secretariat observations on each comment submitted
	3.1	Definition 1	ed	Definition is ambiguous and needs clarifying.	Amend to read '...so that the mains connector to which no connection...'	
	6.4	Paragraph 2	te	The use of the UV photometer as an alternative cannot be supported as serious problems have been encountered in its use in the UK.	Delete reference to UV photometer.	



47D/939/CD

COMMITTEE DRAFT (CD)

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CLOSING DATE FOR COMMENTS:

2022-04-08

SUPERSEDES DOCUMENTS:

47D/927/NP, 47D/930/RVN

IEC SC 47D : SEMICONDUCTOR DEVICES PACKAGING

SECRETARIAT:

Japan

SECRETARY:

Mr Hiroyoshi Yoshida

OF INTEREST TO THE FOLLOWING COMMITTEES:

TC 91

PROPOSED HORIZONTAL STANDARD:

☐

Other TC/SCs are requested to indicate their interest, if any, in this CD to the secretary.

FUNCTIONS CONCERNED:

☐ EMC

☐ ENVIRONMENT

☐ QUALITY ASSURANCE

☐ SAFETY

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Recipients of this document are invited to submit, with their comments, notification of any relevant patent rights of which they are aware and to provide supporting documentation.

TITLE:

Thermal standardization on semiconductor packages – Part 3: Thermal circuit simulation models of semiconductor packages for transient analysis

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INTERNATIONAL ELECTROTECHNICAL COMMISSION

THERMAL STANDARDIZATION ON SEMICONDUCTOR PACKAGES –

Part 3: Thermal circuit simulation models of semiconductor packages for transient analysis

FOREWORD

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IEC 63378-3 has been prepared by subcommittee 47D: Semiconductor devices packaging, of IEC technical committee 47: Semiconductor devices. It is an International Standard.

The text of this International Standard is based on the following documents:

Draft	Report on voting
XX/XX/FDIS	XX/XX/RVD

Full information on the voting for its approval can be found in the report on voting indicated in the above table.

The language used for the development of this International Standard is English.

This document was drafted in accordance with ISO/IEC Directives, Part 2, and developed in accordance with ISO/IEC Directives, Part 1 and ISO/IEC Directives, IEC Supplement, available

94 at www.iec.ch/members_experts/refdocs. The main document types developed by IEC are
95 described in greater detail at www.iec.ch/standardsdev/publications.

96 The committee has decided that the contents of this document will remain unchanged until the
97 stability date indicated on the IEC website under "<http://webstore.iec.ch>" in the data related to
98 the specific document. At this date, the document will be

- 99 • reconfirmed,
- 100 • withdrawn,
- 101 • replaced by a revised edition, or
- 102 • amended.

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